SCES278A - JUNE 1999 - REVISED JUNE 1999

- Member of the Texas Instruments Widebus™ Family
- EPIC™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Typical V_{OLP} (Output Ground Bounce)
 < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot)
 2 V at V_{CC} = 3.3 V, T_A = 25°C
- I_{off} and Power-Up 3-State Support Hot Insertion
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- Latch-Up Performance Exceeds 100 mA Per JESD 78. Class II
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages

description

This 16-bit (dual-octal) noninverting bus transceiver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74LVCZ16245A is designed for asynchronous communication between data buses. The control-function implementation minimizes external timing requirements.

(TOP VIEW) 48 10E 1DIR L 47 🛮 1A1 1B1 🛮 2 1B2 3 46 1 1A2 GND II 4 45 GND 44 🛮 1A3 1B3 🛮 5 1B4 **[**] 6 43 1A4 42 V_{CC} V_{CC} **Ц**7 41 1 1A5 1B5 🛮 8 1B6 **□** 9 40 L 1A6 GND 110 39 GND 1B7 🛮 11 38 🛮 1A7 37 1A8 1B8 **1**2 36 2A1 2B1 13 2B2 14 35 2A2 34 GND GND 15 2B3 📙 16 33 2A3 32 2A4 2B4 🛮 17 V_{CC} 4 18 31 V_{CC} 30 2A5 2B5 🛮 19 29 2A6 2B6 20 GND 21 28 GND 27 2A7 2B7 🛮 22 2B8 🛮 23 26 2A8 2DIR 24 25 20E

DGG OR DL PACKAGE

This device can be used as two 8-bit transceivers or one 16-bit transceiver. It allows data transmission from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable (\overline{OE}) input can be used to disable the device so that the buses are effectively isolated.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

When V_{CC} is between 0 and 1.25 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.25 V, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

This device is fully specified for hot-insertion applications using I_{off} and power-up 3-state. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down. The power-up 3-state circuitry places the outputs in the high-impedance state during power up and power down, which prevents driver conflict.

The SN74LVCZ16245A is characterized for operation from -40°C to 85°C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

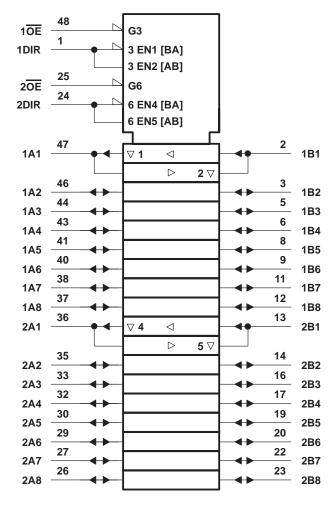
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FUNCTION TABLE (each 8-bit section)

INPUTS		OPERATION				
OE	DIR	OPERATION				
L	L	B data to A bus				
L	Н	A data to B bus				
Н	X	Isolation				

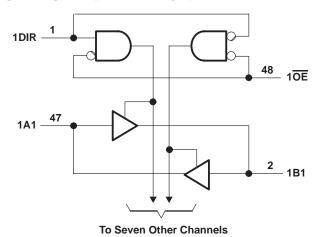
logic symbol†

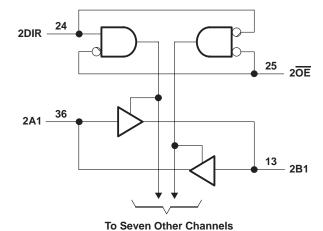


[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



logic diagram (positive logic)





absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC}	–0.5 V to 6.5 V
Input voltage range, V _I : (see Note 1)	–0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, VO	
(see Note 1)	–0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, VO	
(see Notes 1 and 2)	0.5 V to V _{CC} + 0.5 V
Input clamp current, I _{IK} (V _I < 0)	–50 mA
Output clamp current, I _{OK} (V _O < 0)	–50 mA
Continuous output current, IO	±50 mA
Continuous current through each V _{CC} or GND	±100 mA
Package thermal impedance, θ _{JA} (see Note 3): DGG package	89°C/W
DL package	94°C/W
Storage temperature range, T _{stq}	–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
 - 2. The value of V_{CC} is provided in the recommended operating conditions table.
 - 3. The package thermal impedance is calculated in accordance with JESD 51.

SN74LVCZ16245A **16-BIT BUS TRANSCEIVER** WITH 3-STATE OUTPUTS SCES278A – JUNE 1999 – REVISED JUNE 1999

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT	
Vcc	Supply voltage		2.3	3.6	V	
VIH	High-level input voltage $ \frac{V_{CC} = 2.3 \text{ V to } 2.7}{V_{CC} = 2.7 \text{ V to } 3.6} $		1.7		٧	
			2			
\/	Low level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	7 V	
V _{IL}	Low-level input voltage	$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$		0.8	V	
VI	Input voltage		0	5.5	V	
\/a	Output voltage	High or low state	0	VCC	٧	
۷o		3-state	0	5.5		
	High-level output current	V _{CC} = 2.3 V		-8		
ІОН		$V_{CC} = 2.7 V$		-12	mA	
		V _{CC} = 3 V		-24		
		V _{CC} = 2.3 V		8		
l _{OL}	Low-level output current	$V_{CC} = 2.7 V$		12	mA	
	V _{CC} = 3 V			24		
Δt/Δν	Input transition rise or fall rate			5	ns/V	
Δt/ΔV _{CC}	Power-up ramp rate		150		μs/V	
TA	Operating free-air temperature		-40	85	°C	

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARA	METER	TEST CO	ONDITIONS	VCC	MIN	TYP [†]	MAX	UNIT
		I _{OH} = -100 μA		2.3 V to 3.6 V	V _{CC} -0.2			
	$I_{OH} = -8 \text{ mA}$		2.3 V	1.7				
Voн		lou = 12 mA		2.7 V	2.2			V
		I _{OH} = −12 mA		3 V	2.4			
		I _{OH} = -24 mA		3 V	2.2			
		I _{OL} = 100 μA		2.3 V to 3.6 V			0.2	
\ \/ a.		I _{OL} = 8 mA I _{OL} = 12 mA		2.3 V			0.7	٧
VOL				2.7 V			0.4	
		I _{OL} = 24 mA	nA				0.55	
I _I C	ontrol inputs	$V_{I} = 0 \text{ to } 5.5 \text{ V}$		3.6 V			±5	μΑ
l _{off}		V _I or V _O = 5.5 V		0			±10	μΑ
loz‡		V _O = 0 to 5.5 V		3.6 V			±10	μΑ
lozpu		$V_0 = 0.5 \text{ V to } 2.5 \text{ V},$	OE = don't care	0 to 1.25 V			±10	μΑ
IOZPD		$V_O = 0.5 \text{ V to } 2.5 \text{ V},$	OE = don't care	1.25 V to 0			±10	μΑ
Icc		$V_I = V_{CC}$ or GND		0.01/		60		
		$3.6 \text{ V} \le \text{V}_{\text{I}} \le 5.5 \text{ V}$	IO = 0	3.6 V			60	μΑ
Δlcc		One input at V _{CC} – 0.6 V,	Other inputs at V _{CC} or GND	2.7 V to 3.6 V			500	μΑ
C _i C	ontrol inputs	V _I = V _{CC} or GND		3.3 V		5		pF
C _{iO} A	or B ports	VO = VCC or GND		3.3 V		7.5		pF

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 2.7 V		V _{CC} = 3.3 V ± 0.3 V		UNIT
	(INI O1)		MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A or B	B or A	1.3	5.7		4.7	1	4	ns
t _{en}	ŌĒ	A or B	1.8	7.7		6.7	1.5	5.5	ns
^t dis	ŌĒ	A or B	1.8	8.1		7.1	1.5	6.6	ns

operating characteristics, $T_A = 25^{\circ}C$

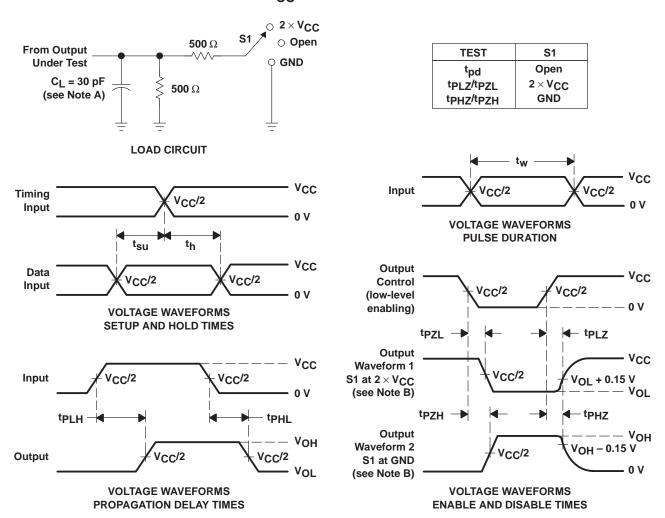
PARAMETER			TEST CONDITIONS	V _{CC} = 2.5 V TYP	V _{CC} = 3.3 V TYP	UNIT
	Power dissipation capacitance per transceiver	Outputs enabled	f 40 MH=	35	42	pF
Cpd		Outputs disabled	f = 10 MHz	4	2	



[†] All typical values are at V_{CC} = 3.3 V, T_A = 25°C. ‡ For I/O ports, the parameter I_{OZ} includes the input leakage current.

[§] This applies in the disabled state only.

PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$



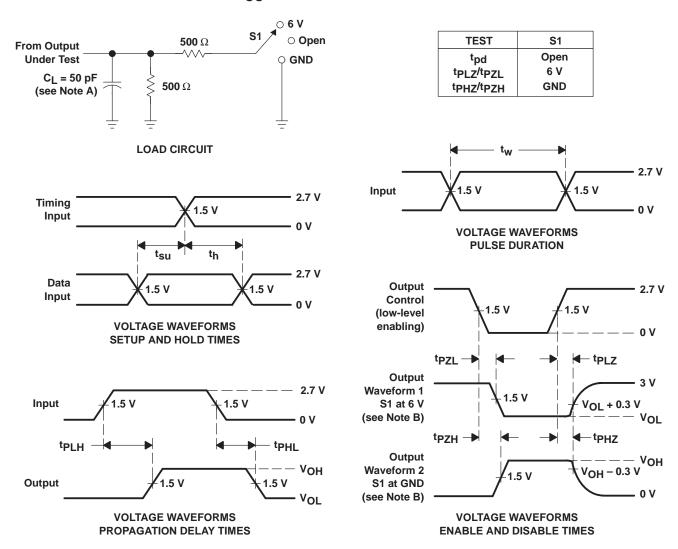
NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq 2$ ns. $t_f \leq 2$ ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLZ and tpHZ are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms



PARAMETER MEASUREMENT INFORMATION V_{CC} = 2.7 V AND 3.3 V \pm 0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq$ 2.5 ns, $t_f \leq$ 2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLZ and tpHZ are the same as tdis.
- F. tpzi and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 2. Load Circuit and Voltage Waveforms

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